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MEMC 99-0900 (2632)
PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Application of Fuerhoff et al.

Art Unit 1765

Serial No. 09/502,340

Filed February 10, 2000

For METHOD AND APPARATUS FOR CONTROLLING DIAMETER OF A SILICON CRYSTAL IN A LOCKED SEED LIFT GROWTH PROCESS

Examiner M. Anderson

June 2, 2003

AMENDMENT D

RECEIVED
JUN 06 2003
TC 1700

TO THE COMMISSIONER FOR PATENTS,

SIR:

In response to the Office action mailed April 2, 2003, please enter the following amendments:

IN THE CLAIMS

Please amend the claims as follows:

Claim 1 (currently amended): A method for use in combination with a crystal growing apparatus for growing a monocrystalline ingot according to the Czochralski process, said crystal growing apparatus having a heated crucible containing a semiconductor melt from which the ingot is grown, said ingot being grown on a seed crystal pulled from the melt, said method comprising the steps of:

defining a temperature model representative of variations in the temperature of the melt in response to variations in power supplied to a heater for heating the melt;